NSN 5961-01-412-7742

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-412-7742 **Inclosure Material:** Plastic **Overall Length:** 4.6 millimeters **Overall Height:** 4.25 millimeters **Overall Width:** 1.6 millimeters Joint Electronic Device Engineering Council/jedec/case Outline Designation: Sot-89 **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 breakdown voltage, dc **Current Rating Per Characteristic:** 50.00 microamperes reverse current, dc **Power Rating Per Characteristic:** 1.0 watts total power dissipation **Capacitance Rating In Picofarads:** 10.0 **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Terminal Type And Quantity:** 3 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:** No